UNISONIC TECHNOLOGIES CO., LTD

UTG4N65-S

Preliminary

Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

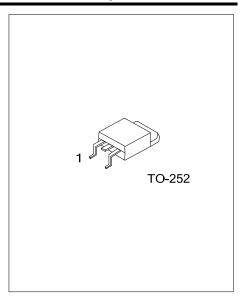
DESCRIPTION

The UTC **UTG4N65-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

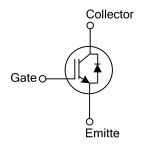
The UTC **UTG4N65-S** is suitable for the resonant or soft switching applications.

■ FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT),Typ.}$ =1.44V @ Ic=4.0A, V_{GE} =15V (T_C =25°C)



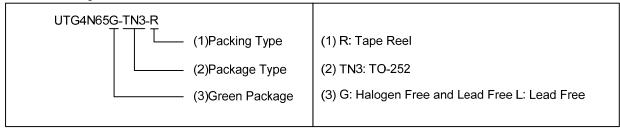
■ SYMBOL



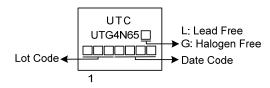
■ ORDERING INFORMATION

Ordering Number		Daalaaaa	Pin Assignment			Da alda a	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTG4N65L-TN3-R	UTG4N65G-TN3-R	TO-252	G	С	E	Tape Reel	

Note: Pin Assignment: G: Gate C: Collector E: Emitter



■ MARKING



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ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V _{CES}	650	V	
Gate-Emitter Voltage		\ <u>/</u>	±20	V	
Transient Gate-emitter voltage (tp < 5 ms)		V_{GES}	±25	V	
Continuous Collector Current	T _C =25°C	Ic	8	Α	
	T _C =100°C		4	Α	
Collector Current Pulsed (Note 1)		I _{CM}	16	Α	
Diode Forward Current	T _C =25°C	l _F	8	Α	
	T _C =100°C		4	Α	
Short Circuit Withstand Time $V_{GE} = 15V, V_{CC} \le 200V$		tsc			
				μs	
Allowed number of short circuits < 1000			3		
Time between short circuits: ≥1.0s					
<i>T</i> _{VJ} = 25°C					
Power Dissipation (T _C =25°C)		P _D	36	W	
Operating Junction Temperature		T_J	-40 ~ +175	°C	
Storage Temperature Range		T _{STG}	-55 ~ +175	°C	

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θјс	3.47	°C/W

^{2.} Pulse width limited by maximum junction temperature.

■ **ELECTRICAL CHARACTERISTICS** (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS			TYP	MAX	UNIT	
Off Characteristics					•	•		
Collector-Emitter Breakdown Voltage	BVces			650			V	
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V				5	μA	
G-E Leakage Current I _{GES}		V _{CE} =0V, V _{GE} =±20V				±100	nA	
On Characteristics								
Gate to Emitter Threshold Voltage	$V_{GE(TH)}$	Ic=250µA, Vce=Vge		4.0		6.5	V	
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =4.0A, V _{GE} =15V	T _C =25°C		1.44	2.1	V	
	(-:)	1	T _C =125°C		1.8		V	
Dynamic Characteristics		<u> </u>			1	1		
Input Capacitance	CIES	 V _{CE} =25V, V _{GE} =0V, f=1MHz			433		pF	
Output Capacitance	Coes				31.5		pF	
Reverse Transfer Capacitance	Cres				7.7		pF	
Switching Characteristics								
Total Gate Charge	\mathbf{Q}_{G}				41.2		nC	
Gate-Emitter Charge	Q_{GE}	V _{CE} =520V, I _C =4.0A, V _{GE} =15V			13.7		nC	
Gate-Collector Charge	Q _{GC}				16.3		nC	
Turn-On Delay Time	t _{DON)}	V _{CC} =400V, I _C =4.0A, R _G =5Ω, V _{GE} =0~15V, L=1000μH			15		ns	
Rise Time	t _R				19		ns	
Turn-Off Delay Time	t _{DOFF)}				39		ns	
Fall Time	t_{F}				290		ns	
Turn-On Switching Loss	Eon				0.154		mJ	
Turn-Off Switching Loss	Eoff	<u> </u>			0.147		mJ	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Forward Voltage Drop	VF	I _F =4.0A			1.49	3.0	V	
Reverse Recovery Time	t _{rr}	I _F =4.0A, dI/dt=100A/μS,			38.1		ns	
Reverse Recovery Charge	Qrr	Vcc=400V			29.6		nC	

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